

K Rim

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11757274/publications.pdf>

Version: 2024-02-01

16
papers

933
citations

933447

10
h-index

1058476

14
g-index

16
all docs

16
docs citations

16
times ranked

567
citing authors

#	ARTICLE	IF	CITATIONS
1	Fabrication and analysis of deep submicron strained-Si n-MOSFET's. IEEE Transactions on Electron Devices, 2000, 47, 1406-1415.	3.0	328
2	Measurement of the effect of self-heating in strained-silicon MOSFETs. IEEE Electron Device Letters, 2002, 23, 360-362.	3.9	135
3	Strained Si CMOS (SS CMOS) technology: opportunities and challenges. Solid-State Electronics, 2003, 47, 1133-1139.	1.4	82
4	Strained Si NMOSFETs for high performance CMOS technology. , 0, , .		79
5	Enhanced hole mobilities in surface-channel strained-Si p-MOSFETs. , 0, , .		60
6	Effect of thermal processing on strain relaxation and interdiffusion in Si/SiGe heterostructures studied using Raman spectroscopy. Applied Physics Letters, 2001, 79, 2148-2150.	3.3	57
7	The revolution in SiGe: impact on device electronics. Applied Surface Science, 2004, 224, 9-17.	6.1	47
8	Comparison of Si/Si _{1-x} Ge _x and Si/Si _{1-y} Cy heterojunctions grown by rapid thermal chemical vapor deposition. Thin Solid Films, 1998, 321, 41-46.	1.8	30
9	Measurement of the conduction band offsets in Si/Si _{1-x} Ge _x and Si/Si _{1-y} Cy heterostructures using metal-oxide-semiconductor capacitors. Journal of Applied Physics, 1999, 85, 978-984.	2.5	27
10	Evaluation of the valence band discontinuity of Si/Si _{1-x} Ge _x /Si heterostructures by application of admittance spectroscopy to MOS capacitors. IEEE Transactions on Electron Devices, 1998, 45, 494-501.	3.0	26
11	Admittance spectroscopy analysis of the conduction band offsets in Si/Si _{1-x} Ge _x and Si/Si _{1-y} Cy heterostructures. Journal of Applied Physics, 1999, 85, 985-993.	2.5	23
12	Metal-oxide-semiconductor capacitance-voltage characteristics and band offsets for Si _{1-y} Cy/Si heterostructures. Applied Physics Letters, 1998, 72, 2286-2288.	3.3	15
13	N-channel MOSFETs fabricated on He-implanted and annealed SiGe buffer layers. Solid-State Electronics, 2005, 49, 1669-1673.	1.4	10
14	Characteristics of Surface-Channel Strained Si _{1-y} Cy-MOSFETs. Materials Research Society Symposia Proceedings, 1998, 533, 43.	0.1	7
15	Epitaxial Growth And Electronic Characterization Of Carboncontaining Silicon-Based Heterostructures. Materials Research Society Symposia Proceedings, 1998, 533, 263.	0.1	6
16	Rapid Thermal Processing-Based Heteroepitaxy: Material and Device Challenges. Materials Research Society Symposia Proceedings, 1995, 387, 299.	0.1	1